

VHF power transistor

BLW30

Description:

NPN silicon planar epitaxial transistor encapsulated in a 4-lead 3/8 inch SOT120 capstan envelope with a ceramic cap. It is designed for common emitter, class-B operation mobile VHF transmitters with a supply voltage of 12.5 V.

Features:

- * Emitter-ballasting resistors for an optimum temperature profile
- * Excellent reliability
- * Withstands full load mismatch.

Data:

MODE OF OPERATION	f (MHz)	V _{CE} (V)	P _L (W)	G _p (dB)	η _c (%)
c.w. class-B	175	12.5	30	> 10	> 55

Drawings:

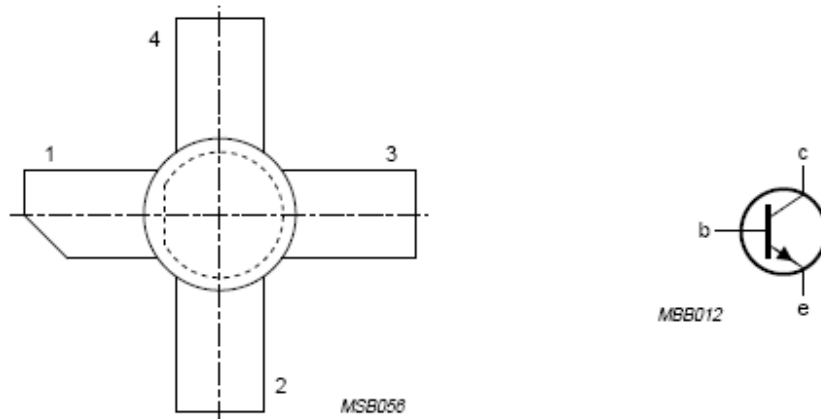


Fig.1 Simplified outline and symbol.

PIN	DESCRIPTION
1	collector
2	emitter
3	base
4	emitter